



ON Semiconductor®

FDG6301N-F085

Dual N-Channel, Digital FET

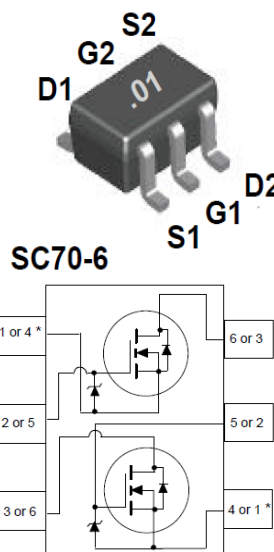
Features

- 25 V, 0.22 A continuous, 0.65 A peak.
- $R_{DS(ON)} = 4 \Omega$ @ $V_{GS} = 4.5$ V,
- $R_{DS(ON)} = 5 \Omega$ @ $V_{GS} = 2.7$ V.
- Very low level gate drive requirements allowing direct operation in 3 V circuits ($V_{GS(th)} < 1.5$ V).
- Gate-Source Zener for ESD ruggedness (>6kV Human Body Model).
- Compact industry standard SC70-6 surface mount package.
- Qualified to AEC Q101
- RoHS Compliant



Applications

- Low voltage applications as a replacement for bipolar digital transistors and small signal MOSFETs



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain to Source Voltage	25	V
V_{GS}	Gate to Source Voltage	8	V
I_D	Drain Current Continuous	0.22	A
	Pulsed	0.65	
P_D	Power Dissipation	0.3	W
T_J, T_{STG}	Operating and Storage Temperature	-55 to +150	$^\circ\text{C}$
ESD	Electrostatic Discharge Rating MIL-STD-883D Human Body Model(100 pF / 1500 W)	6.0	kV
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	415	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDG6301N	FDG6301N-F085	SC70-6	7"	8mm	3000 units

Notes:

1: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder

mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design, while $R_{\theta JA}$ is determined by the board design. $R_{\theta JA} = 415$ $^\circ\text{C/W}$ on minimum pad mounting on FR-4 board in still air

2: A suffix as "...F085P" has been temporarily introduced in order to manage a double source strategy as ON Semiconductor has officially announced in Aug 2014.

3: Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%.

FDG6301N-F085 Dual N-Channel Digital FET

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

$B_{V_{DSS}}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	25	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 20\text{V}$, $V_{GS} = 0\text{V}$ $T_J = 55^\circ\text{C}$	-	-	1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 8\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu\text{A}$	0.65	0.85	1.5	V
$r_{DS(on)}$	Drain to Source On Resistance	$I_D = 0.22\text{A}$, $V_{GS} = 4.5\text{V}$	-	2.6	4	Ω
		$I_D = 0.19\text{A}$, $V_{GS} = 2.7\text{V}$	-	3.7	5	
		$I_D = 0.22\text{A}$, $V_{GS} = 4.5\text{V}$ $T_J = 125^\circ\text{C}$	-	5.3	7	
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 4.5\text{V}$, $V_{DS} = 5\text{V}$	0.22	-	-	
g_{FS}	Forward Transconductance	$I_D = 0.22\text{A}$, $V_{DS} = 5\text{V}$	-	0.2	-	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 10\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$	-	9.5	-	pF
C_{oss}	Output Capacitance		-	6	-	pF
C_{rss}	Reverse Transfer Capacitance		-	1.3	-	pF
$Q_{g(TOT)}$	Total Gate Charge at -4.5V	$V_{GS} = 0$ to 4.5V	-	0.29	0.4	nC
Q_{gs}	Gate to Source Gate Charge	$V_{DD} = 5\text{V}$ $I_D = 0.22\text{A}$	-	0.12	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	0.03	-	nC

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 5\text{V}$, $I_D = 0.5\text{A}$ $V_{GS} = 4.5\text{V}$, $R_{GEN} = 50\Omega$	-	5	10	ns
t_r	Rise Time		-	4.5	10	ns
$t_{d(off)}$	Turn-Off Delay Time		-	4	8	ns
t_f	Fall Time		-	3.2	7	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Source Current		-	-	0.25	A
V _{SD}	Source to Drain Diode Voltage	I _{SD} = 0.25A, V _{GS} = 0V	-	0.8	1.2	V

Typical Characteristics

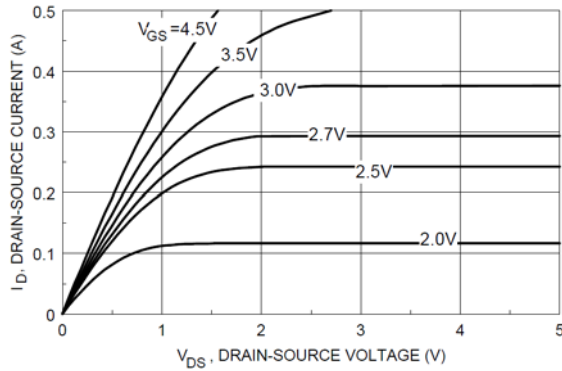


Figure 1. On-Region Characteristics.

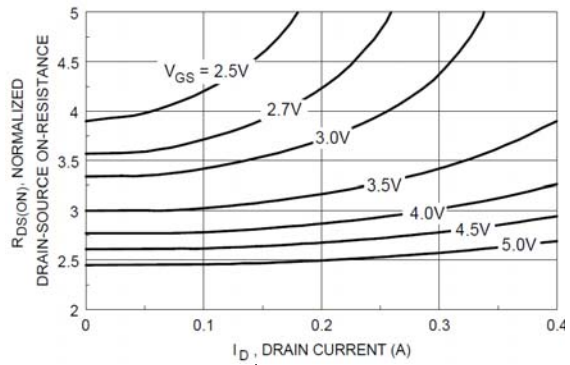


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

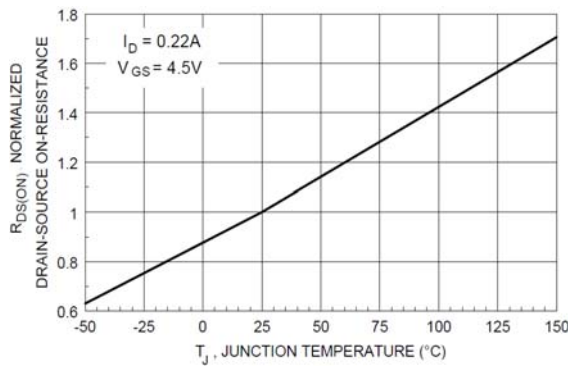


Figure 3. On-Resistance Variation with Temperature.

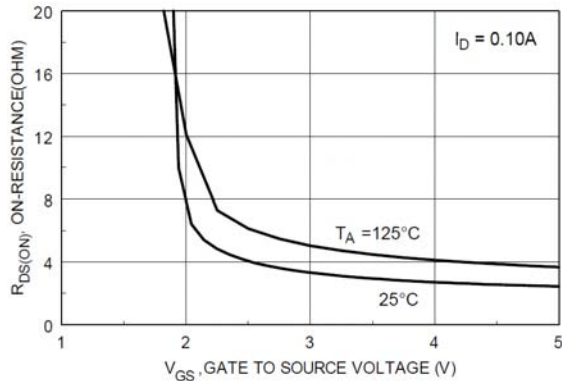


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

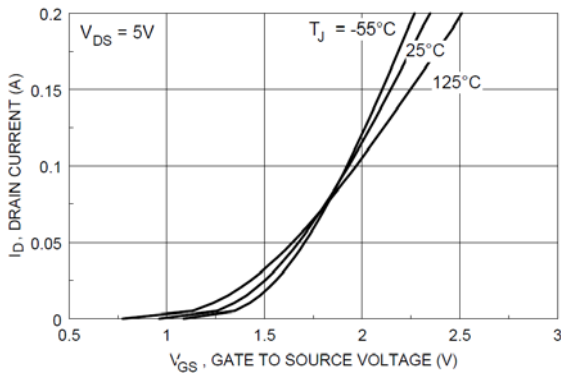


Figure 5. Transfer Characteristics.

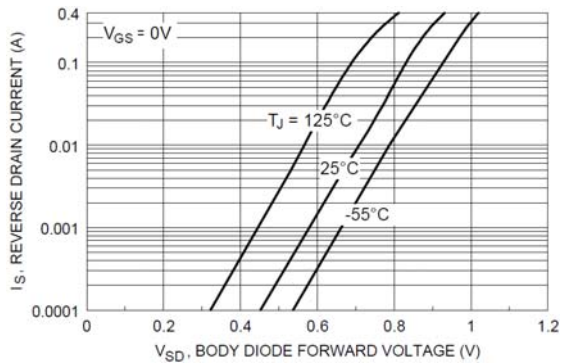


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

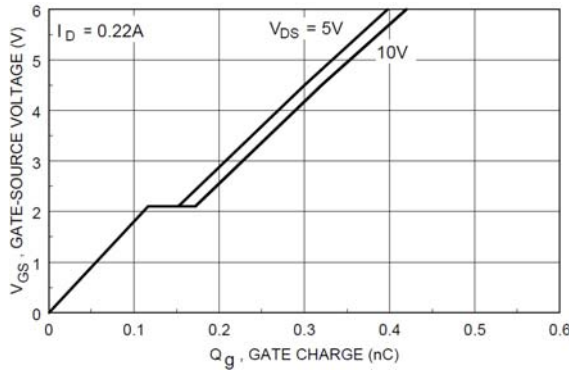


Figure 7. Gate Charge Characteristics.

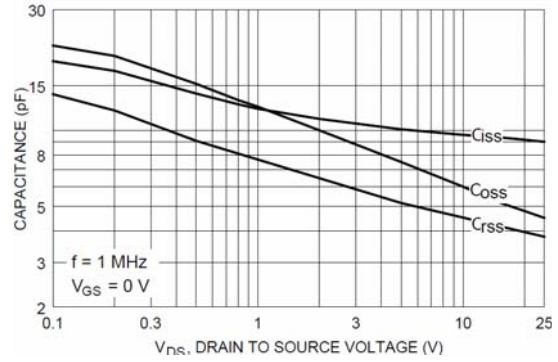


Figure 8. Capacitance Characteristics.

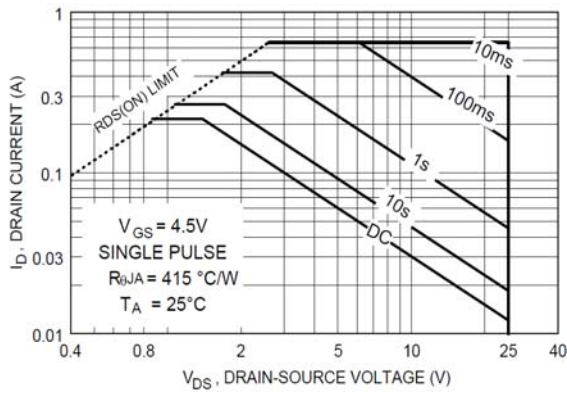


Figure 9. Maximum Safe Operating Area.

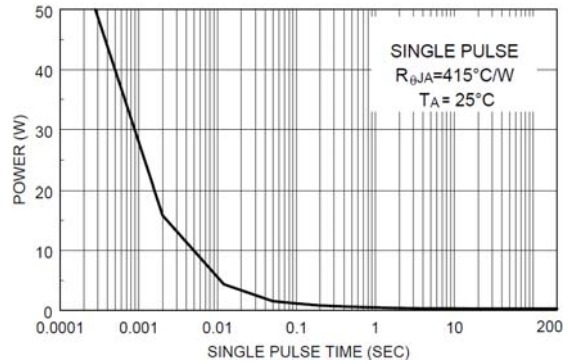


Figure 10. Single Pulse Maximum Power Dissipation.

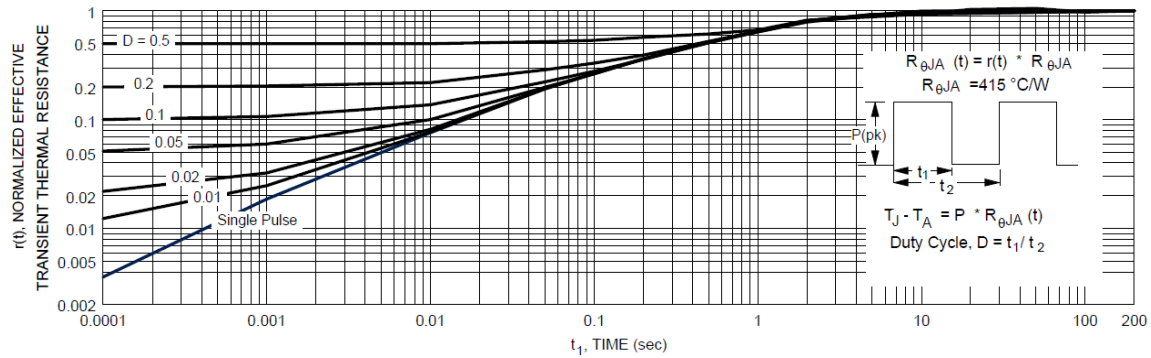


Figure 11. Transient Thermal Response Curve.

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